

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A method comprising:
over an area of a substrate, forming a plurality of three dimensional first structures each including lateral side portions defining a thickness of the plurality of first structures and a distance from the surface of the substrate;
following forming the plurality of first structures, conformally introducing a sacrificial material over the area of the substrate including on the lateral side portions of the plurality of first structures;
introducing a second structural material over the sacrificial material;
after introducing the second structural material, exposing a portion of the sacrificial material and a ~~superior~~-surface of the plurality of first structures, the ~~superior~~-surface opposing the surface of the substrate; and
removing the sacrificial material,
wherein removing the sacrificial material comprises suspending the second structural material as a second structure electrically coupled to the first structure.
2. (Canceled)
3. (Previously Presented) The method of claim 1, wherein exposing a portion of the sacrificial material comprises removing a portion of the second structural material.
4. (Original) The method of claim 1, prior to introducing the second structural material, further comprising patterning the sacrificial material.
5. (Original) The method of claim 1, wherein the first structural material comprises silicon and the sacrificial material comprises silicon dioxide and introducing the sacrificial material comprises growing.
6. (Canceled)
7. (Original) The method of claim 1, wherein patterning the first structures defines a plurality of first areas of the portion of the substrate occupied by the first structures and at least a second area of the portion of the substrate free of the first structures, and introducing the sacrificial material comprises introducing the sacrificial material at least over the second area.

8. (Currently Amended) A method comprising:
over an area of a surface of a substrate, lithographically patterning a plurality of first structures each including lateral side portions defining a thickness of the plurality of first structures and a distance from the surface of the substrate, the plurality of first structures having a first dimension about the surface of the substrate and a second different dimension;
following forming the plurality of first structures, conformally introducing a sacrificial material layer over the area of the substrate including on the lateral side portions of the plurality of first structures;
patterning the sacrificial material to expose a ~~superior~~ surface of the plurality of first structures, the ~~superior~~ surface opposing the surface of the substrate;
forming second structures over the sacrificial material; and
removing the sacrificial material,
wherein removing the sacrificial material comprises suspending the second structure by the first structure, and wherein the second structure is electrically coupled to the first structure.
9. (Canceled)
10. (Original) The method of claim 8, prior to removing the sacrificial material, further comprising exposing a portion of the sacrificial material.
11. (Previously Presented) The method of claim 10, wherein exposing a portion of the sacrificial material comprises removing a portion of the second structural material.
12. (Original) The method of claim 8, wherein the sacrificial material comprises silicon dioxide and introducing the sacrificial material comprises growing.

Claims 13-17 (Canceled)